

TRANSISTOR (PNP)

FEATURES

Low speed switching

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

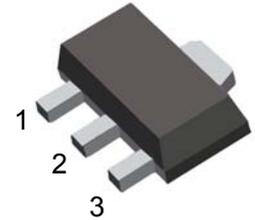
Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	-3	A
P _C	Collector Power Dissipation	0.5	W
R _{θJA}	Thermal Resistance, junction to Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

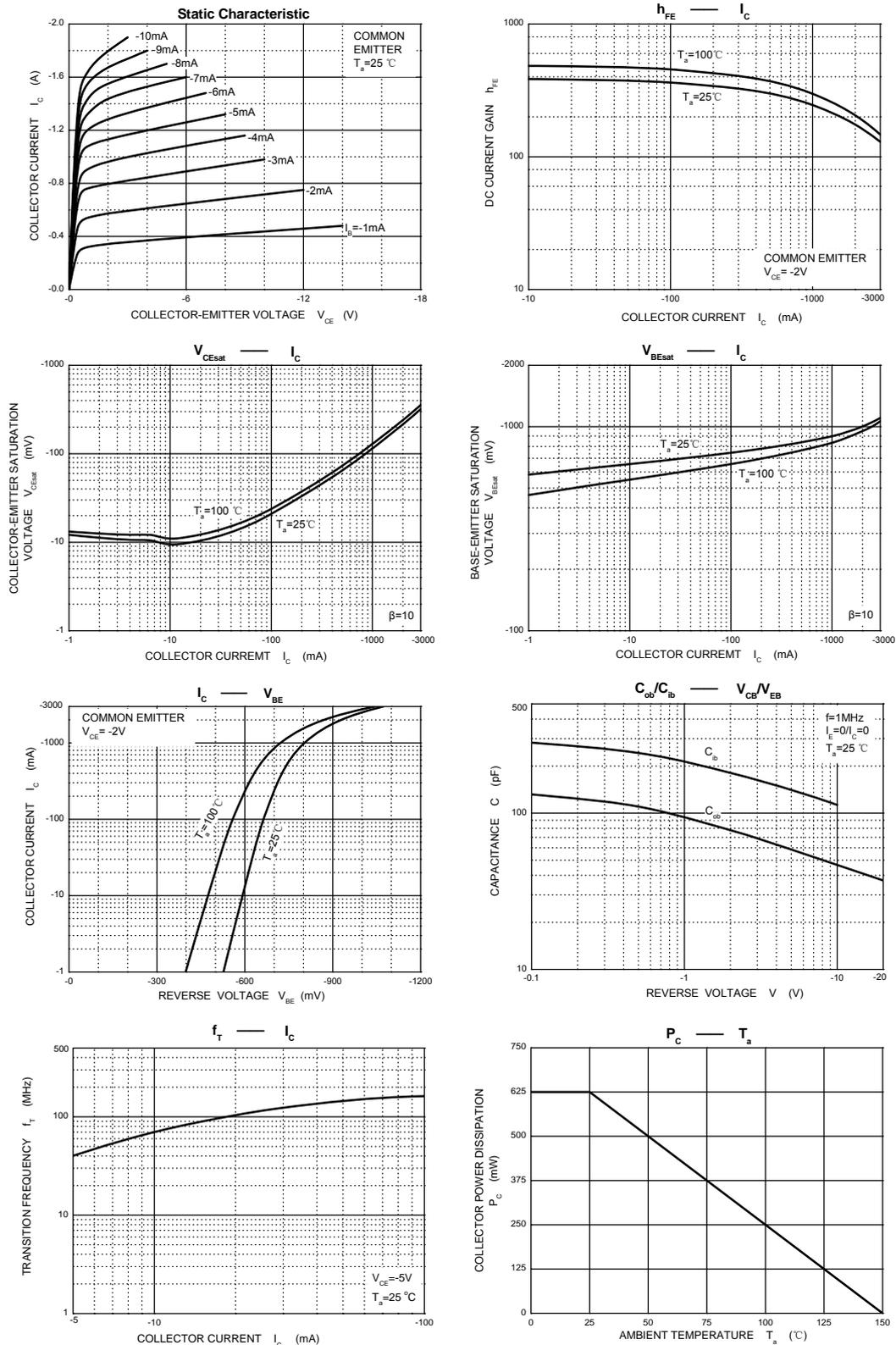
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} = -5V, I _C =-0.1A f =10MHz		80		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

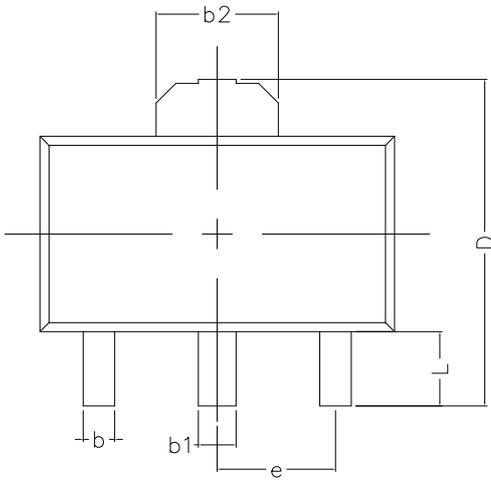
TRANSISTOR (PNP)

Typical characteristics

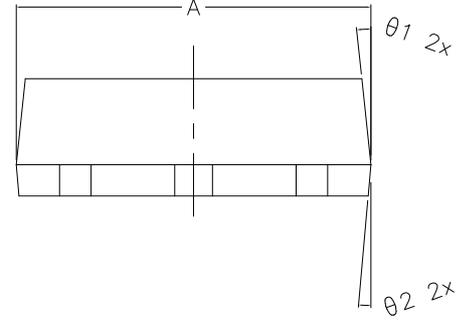
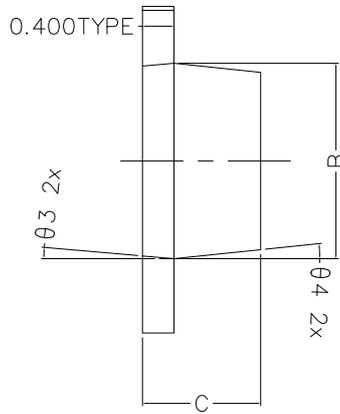




TRANSISTOR (PNP)



TOP VIEW



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.450	4.550	4.650
B	2.450	2.550	2.650
C	1.400	1.500	1.600
D	4.100	4.200	4.300
L	0.850	0.950	1.050
b	0.350	0.400	0.450
b1	0.430	0.480	0.530
b2	1.500	1.550	1.600
e	1.500TYPE		
$\theta 1$	6° TYPE		
$\theta 2$	5° TYPE		
$\theta 3$	5° TYPE		
$\theta 4$	6° TYPE		